

5b  
C3  
P2

11. (Amended) A method for producing porous silicon, the method consisting of the following steps:

depositing a thin discontinuous layer of metal on a Si surface;

forming the porous silicon by etching the Si surface in a HF and oxidant solution for a period of about two seconds up to 60 minutes, said etching being conducted without external electrical bias.

B3

21. (Amended) A method for producing porous silicon, the method comprising steps of:

depositing metal on a Si surface in a thickness sufficient to permit nucleation that forms nanometer size metal particles and small enough to prevent formation of a continuous metal layer;

forming the porous silicon by etching the Si surface in a HF and oxidant solution for a period of about two seconds up to 60 minutes, said etching being conducted without external electrical bias.

### REMARKS

Claims 1-7, 9, 10-17, 19, and 20 stand rejected under 35 U.S.C. § 103(a) as being unpatentable over Russell in view of Yoshikawa. Claims 8 and 18 stand rejected under 35 U.S.C. § 103(a) as being unpatentable over Russell in view of Yoshikawa, and further in